

ABSTRACT OF THE DISCLOSURE

There is provided a high-frequency GaAs power FET element with high performance, capable of suppressing an abnormal oscillation. Thin film resistors are provided so as to be connected electrically between incoming distributed constant lines connected electrically to FET chips, and thin film resistors are provided so as to be connected electrically between outgoing distributed constant lines electrically connected to FET chips. An unnecessary roundabout power is consumed by the thin film transistors in the incoming distributed constant lines and the outgoing distributed constant lines.